

20V Dual N-Channel MOSFET



SOP-8

Pin Definition:



- 1. Source 1
- 2. Gate 1 3. Source 2
- 4. Gate 2
- 5, 6, 7, 8. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)		
20	30 @ V _{GS} = 4.5V	6.0		
	40 @ V _{GS} = 2.5V	5.2		

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

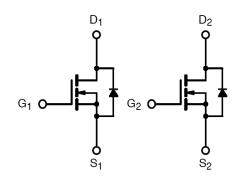
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM9428DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol Limit			Unit	
Drain-Source Voltage	ge		20	V	
Gate-Source Voltage	Itage		±8	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	6	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM} 20		А	
Continuous Source Current (Diode Condu	iction) ^{a,b}	I _S	1.7	А	
Maximum Dower Discipation	Ta = 25°C	Ь	2.5	W	
Maximum Power Dissipation	Ta = 70°C	P _D	1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Tempera	perating Junction and Storage Temperature Range		-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	R⊖ _{JF}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



20V Dual N-Channel MOSFET

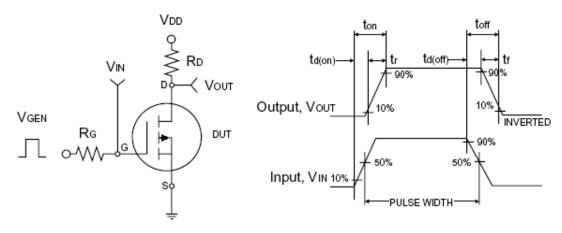


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	1					I
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.45	0.65	0.85	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	V _{DS} ≥5V, V _{GS} = 4.5V	I _{D(ON)}	20			Α
Dunin Causea On State Besistance	$V_{GS} = 4.5V, I_D = 6.0A$	В		23	30	mΩ
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.2A$	$R_{DS(ON)}$		28	40	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.0A$	g _{fs}		24		S
Diode Forward Voltage	I _S = 1.0A, V _{GS} = 0V	V_{SD}			1.2	V
Dynamic ^b				_	_	
Total Gate Charge	$V_{DS} = 10V, I_D = 6A,$	Q_g		11	14	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_gs		1.5		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_{gd}		2.1		
Input Capacitance	\\ -40\\\\ -0\\	C _{iss}		900		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	C _{oss}		140		pF
Reverse Transfer Capacitance		C _{rss}		100		
Switching ^c						
Turn-On Delay Time	V = 40V D = 400	t _{d(on)}		0.53	0.8	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$	t _r		1.4	2.2	20
Turn-Off Delay Time	$I_D = 1A$, $V_{GEN} = 4.5V$,	t _{d(off)}		13.5	20	nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t _f		5.9	9	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

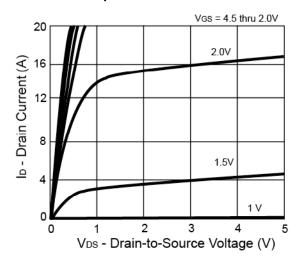


20V Dual N-Channel MOSFET

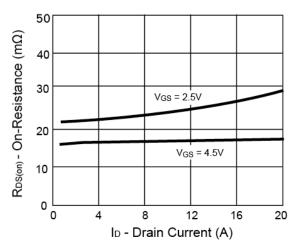


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

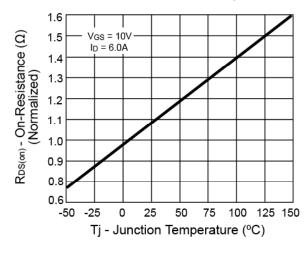
Output Characteristics



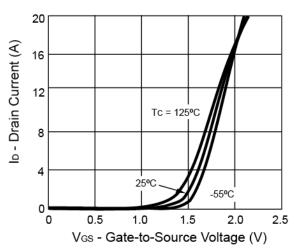
On-Resistance vs. Drain Current



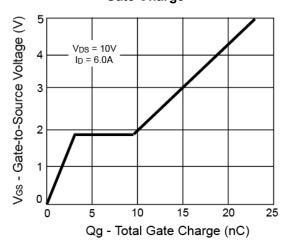
On-Resistance vs. Junction Temperature



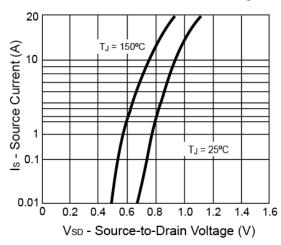
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





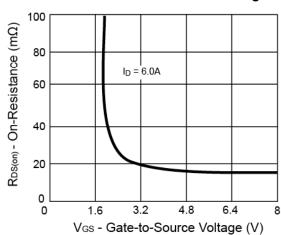


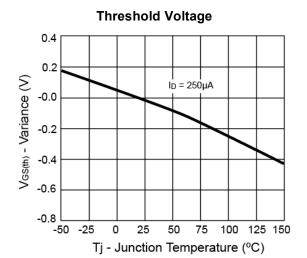
20V Dual N-Channel MOSFET



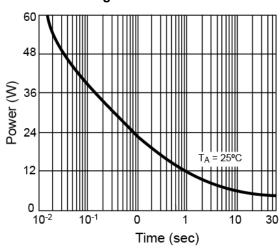
Electrical Characteristics Curve (Ta = 25 C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

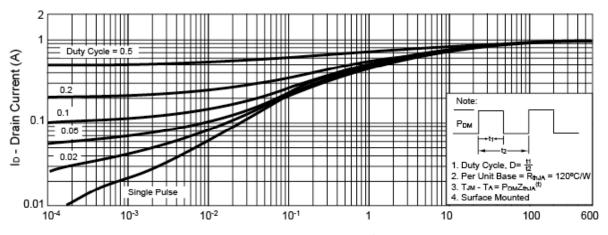




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



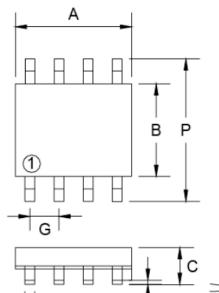
Square Wave Pulse Duration (sec)



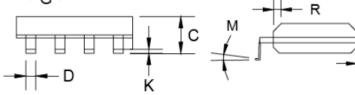




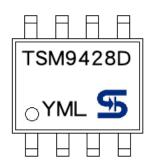
SOP-8 Mechanical Drawing



	SOP-8 DIMENSION				
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05BSC		
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



Marking Diagram



Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



TSM9428D 20V Dual N-Channel MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.